

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSII)

2SK3389

Switching Regulator, DC-DC Converter Applications
Motor Drive Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 3.8 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 70 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu\text{A}$ ($V_{DS} = 30 \text{ V}$)
- Enhancement-mode: $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	75	A
	Pulse (Note 1)	I_{DP}	300	
Drain power dissipation		P_D	125	W
Single pulse avalanche energy (Note 2)		E_{AS}	731	mJ
Avalanche current		I_{AR}	75	A
Repetitive avalanche energy (Note 3)		E_{AR}	12.5	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

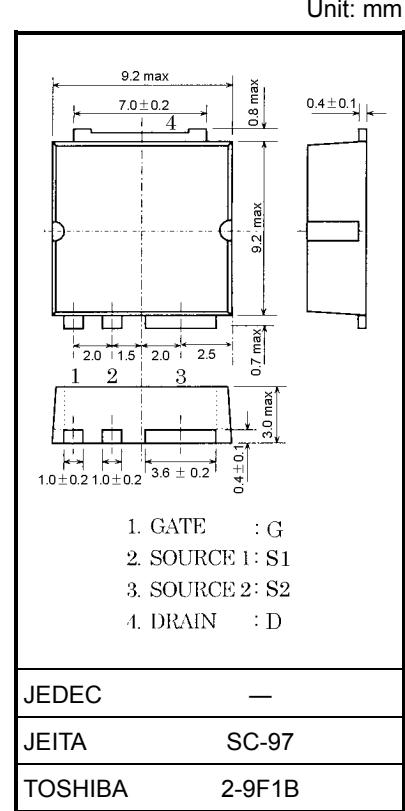
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th}(\text{ch-c})$	1.00	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 95 \mu\text{H}$, $I_{AR} = 75 \text{ A}$, $R_G = 25 \Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

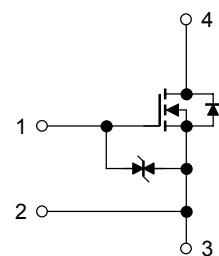
This transistor is an electrostatic sensitive device. Please handle with caution.



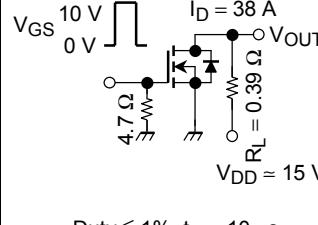
Weight: 0.74 g (typ.)

Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.



Electrical Characteristics (Note 4) (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	—	—	±10	μA	
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	—	—	100	μA	
Drain-source breakdown voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	30	—	—	V	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	—	4.0	V	
Drain-source ON resistance	R _{Ds (ON)}	V _{GS} = 10 V, I _D = 38 A	—	3.8	5.0	mΩ	
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 38 A	35	70	—	S	
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	—	3530	—	pF	
Reverse transfer capacitance	C _{rss}		—	570	—		
Output capacitance	C _{oss}		—	1870	—		
Switching time	Rise time	t _r	 Duty ≤ 1%, t _W = 10 μs	—	10	—	ns
	Turn-on time	t _{on}		—	25	—	
	Fall time	t _f		—	20	—	
	Turn-off time	t _{off}		—	65	—	
Total gate charge (gate-source plus gate-drain)	Q _g	V _{DD} = 24 V, V _{GS} = 10 V, I _D = 75 A	—	62	—	nC	
Gate-source charge	Q _{gs}		—	43	—		
Gate-drain ("miller") charge	Q _{gd}		—	19	—		

Note 4: Please connect the S1 pin and S2 pin, and then ground the connected pin.
 (However, while switching times are measured, please don't connect and ground it.)

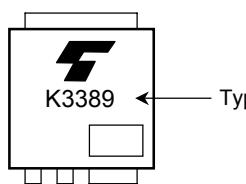
Source-Drain Ratings and Characteristics (Note 5) (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1, Note 5)	I _{DR1}	—	—	—	75	A
Pulse drain reverse current (Note 1, Note 5)	I _{DRP1}	—	—	—	300	A
Continuous drain reverse current (Note 1, Note 5)	I _{DR2}	—	—	—	1	A
Pulse drain reverse current (Note 1, Note 5)	I _{DRP2}	—	—	—	4	A
Forward voltage (diode)	V _{DS2F}	I _{DR1} = 75 A, V _{GS} = 0 V	—	—	-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 75 A, V _{GS} = 0 V, dI _{DR} /dt = 50 A/μs	—	120	—	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 50 A/μs	—	180	—	nC

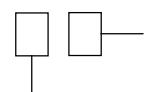
Note 5: drain, flowing current value between the S2 pin, open the S1 pin
 drain, flowing current value between the S1 pin, open the S2 pin

Unless otherwise specified, please connect the S1 and S2 pins, and then ground the connected pin.

Marking



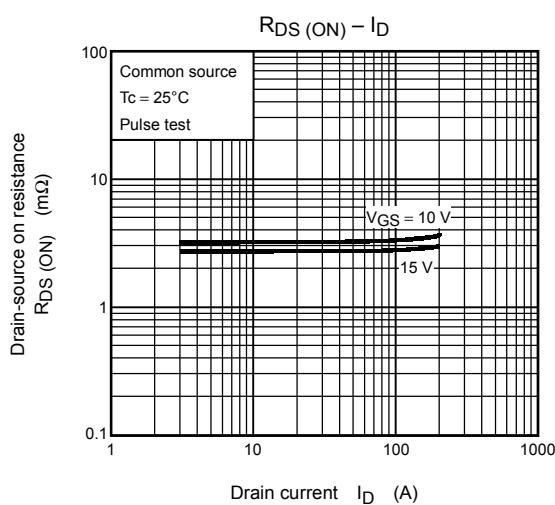
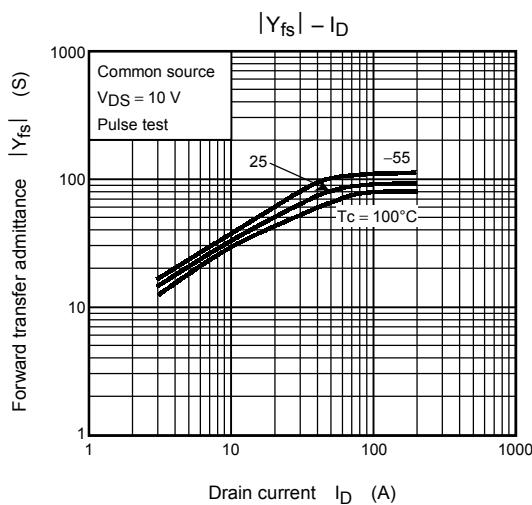
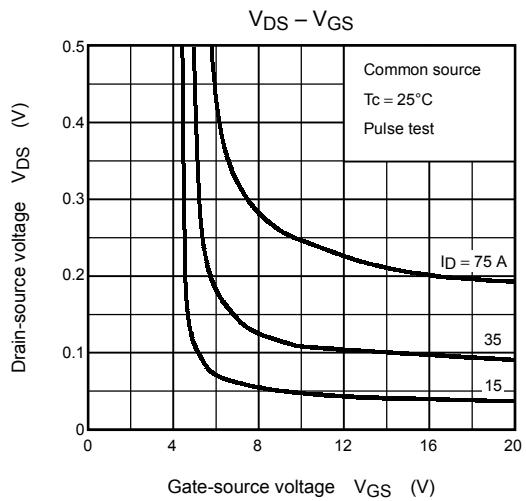
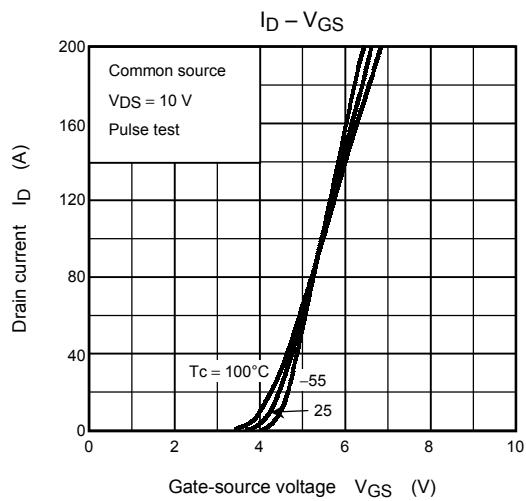
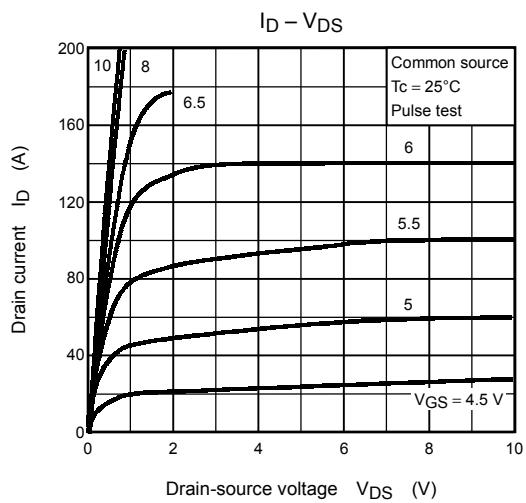
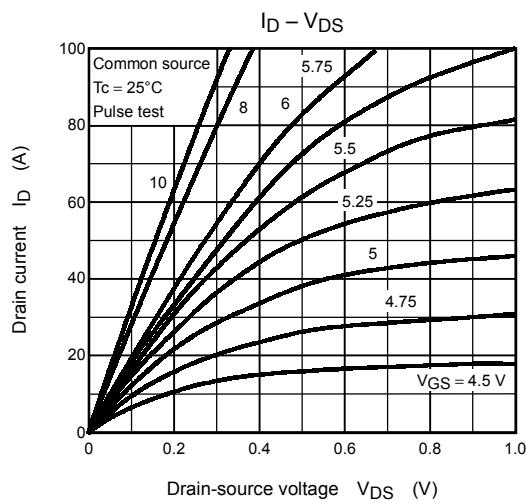
Lot Number

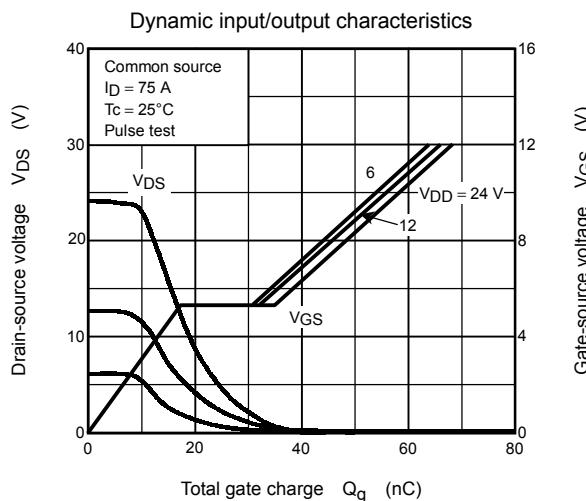
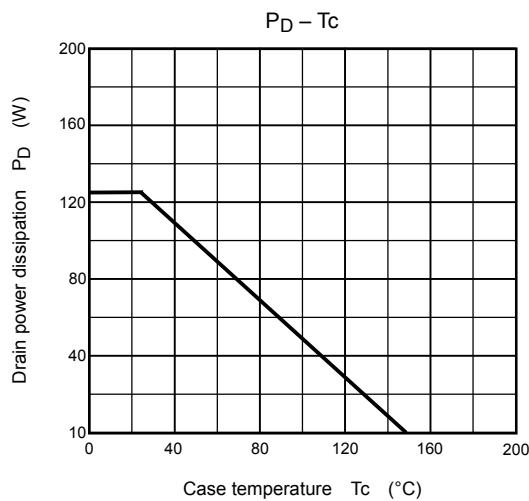
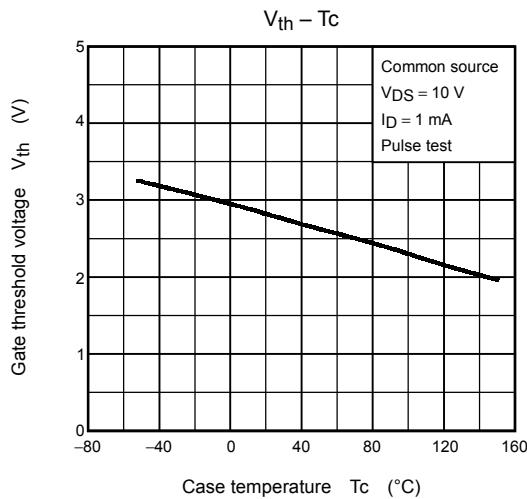
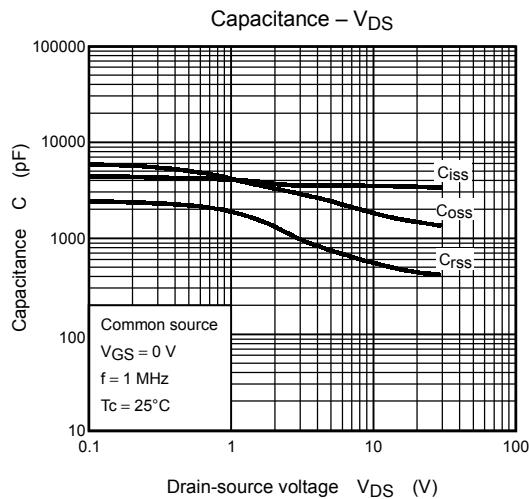
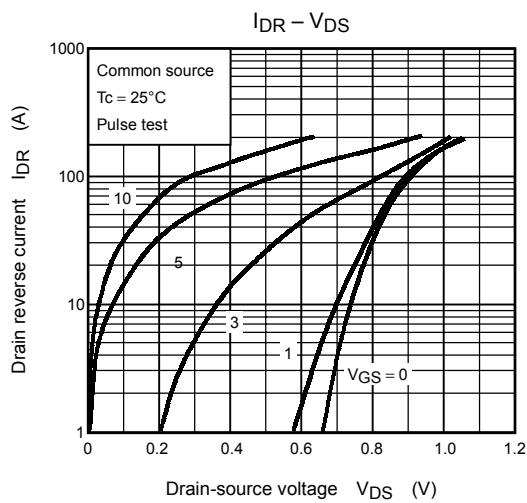
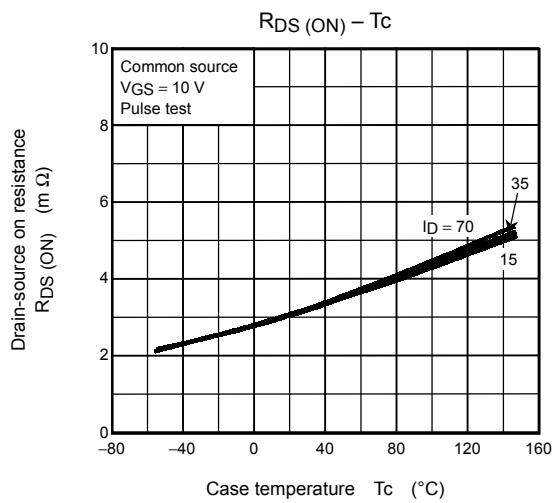


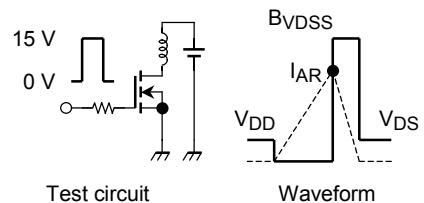
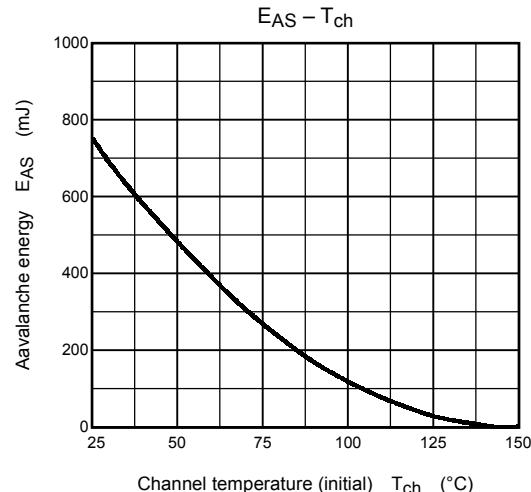
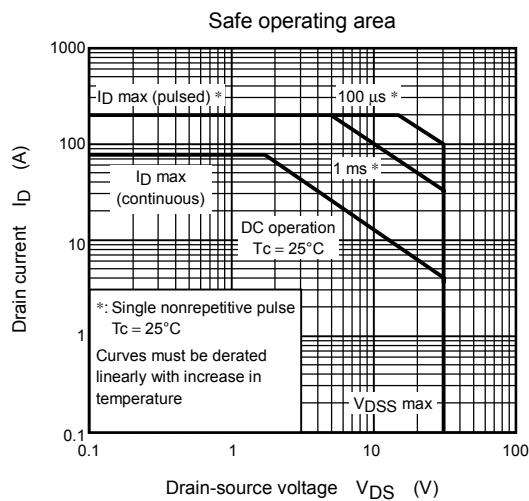
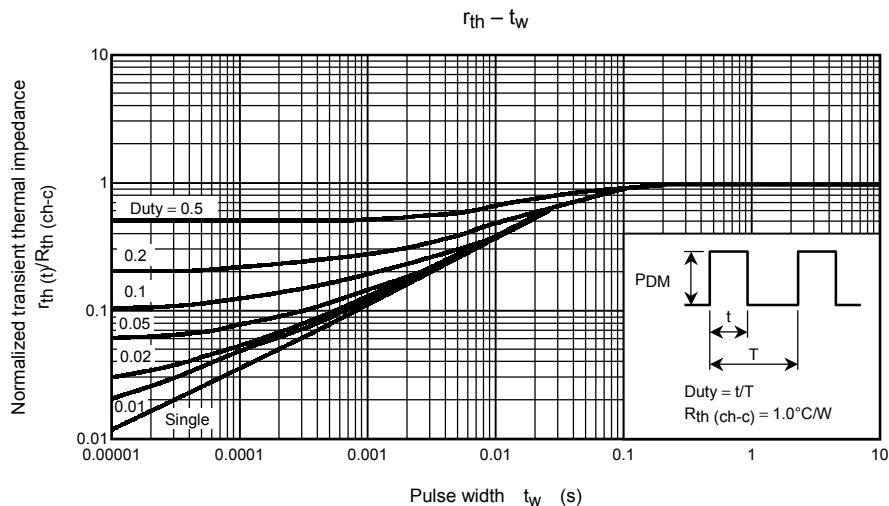
Month (starting from alphabet A)



Year (last number of the christian era)







$$R_G = 25 \Omega$$

$$V_{DD} = 25 \text{ V}, L = 95 \mu\text{H}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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